

MOS INTEGRATED CIRCUIT

μ PD42S4170L, 424170L

4 M-BIT DYNAMIC RAM

256K-WORD BY 16-BIT, FAST PAGE MODE, BYTE WRITE MODE

DESCRIPTION

The μ PD42S4170L, 424170L are 262 144 words by 16 bits dynamic CMOS RAMs with optional fast page mode and byte write mode.

High performance CMOS sense amplifier, peripheral circuits and one transistor dynamic memory cell technique realize high speed access and low power consumption.

In addition to this, refresh is accomplished by performing CAS before $\overline{\text{RAS}}$ self refresh on the μ PD42S4170L.

The μ PD42S4170L and μ PD424170L are packaged in 44-pin plastic TSOP, 40-pin plastic SOJ and 40-pin plastic ZIP.

FEATURES

- 262 144 words by 16 bits organization
- Fast access and cycle time

Part number	Refresh cycle	Power consumption Active (MAX.)	Access time (MAX.)	R/W cycle time (MIN.)	Fast page mode cycle time (MIN.)
μ PD42S4170L-A70	1 024 cycles/128 ms	324.0 mW	70 ns	130 ns	45 ns
μ PD424170L-A70	1 024 cycles/ 16 ms				
μ PD42S4170L-A80	1 024 cycles/128 ms	288.0 mW	80 ns	150 ns	50 ns
μ PD424170L-A80	1 024 cycles/ 16 ms				
μ PD42S4170L-A10	1 024 cycles/128 ms	252.0 mW	100 ns	180 ns	60 ns
μ PD424170L-A10	1 024 cycles/ 16 ms				

- Low power consumption
 - Standby (CMOS level input) 0.36 mW MAX. (μ PD42S4170L)
 - 1.8 mW MAX. (μ PD424170L)
- Single +3.3 V \pm 0.3 V power supply
- Fast page mode and byte write mode capability
- The μ PD42S4170L has 4 types of refresh
 - CAS before $\overline{\text{RAS}}$ internal address self refresh, $\overline{\text{RAS}}$ only refresh, hidden refresh and CAS before $\overline{\text{RAS}}$ internal address refresh
- The μ PD424170L has 3 types of refresh
 - RAS only refresh, hidden refresh and $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ internal address refresh
- Multiplexed address inputs ... Row address: A0 to A9, Column address: A0 to A7
- On-chip substrate bias generator

The information in this document is subject to change without notice.

The mark ★ shows revised points.

★ ORDERING INFORMATION

Part number	Access time (MAX.)	Package	Refresh
μPD42S4170LG5-A70-7JF	70 ns	44-pin Plastic TSOP	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ self refresh $\overline{\text{RAS}}$ only refresh $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh hidden refresh
μPD42S4170LG5-A80-7JF	80 ns		
μPD42S4170LG5-A10-7JF	100 ns		
μPD42S4170LG5-A70-7KF	70 ns	44-pin Plastic TSOP (Reverse bent)	
μPD42S4170LG5-A80-7KF	80 ns		
μPD42S4170LG5-A10-7KF	100 ns		
μPD42S4170LLE-A70	70 ns	40-pin Plastic SOJ	
μPD42S4170LLE-A80	80 ns		
μPD42S4170LLE-A10	100 ns		
μPD42S4170LV-A70	70 ns	40-pin Plastic ZIP	
μPD42S4170LV-A80	80 ns		
μPD42S4170LV-A10	100 ns		
μPD424170LG5-A70-7JF	70 ns	44-pin Plastic TSOP	$\overline{\text{RAS}}$ only refresh $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh hidden refresh
μPD424170LG5-A80-7JF	80 ns		
μPD424170LG5-A10-7JF	100 ns		
μPD424170LG5-A70-7KF	70 ns	44-pin Plastic TSOP (Reverse bent)	
μPD424170LG5-A80-7KF	80 ns		
μPD424170LG5-A10-7KF	100 ns		
μPD424170LLE-A70	70 ns	40-pin Plastic SOJ	
μPD424170LLE-A80	80 ns		
μPD424170LLE-A10	100 ns		
μPD424170LV-A70	70 ns	40-pin Plastic ZIP	
μPD424170LV-A80	80 ns		
μPD424170LV-A10	100 ns		

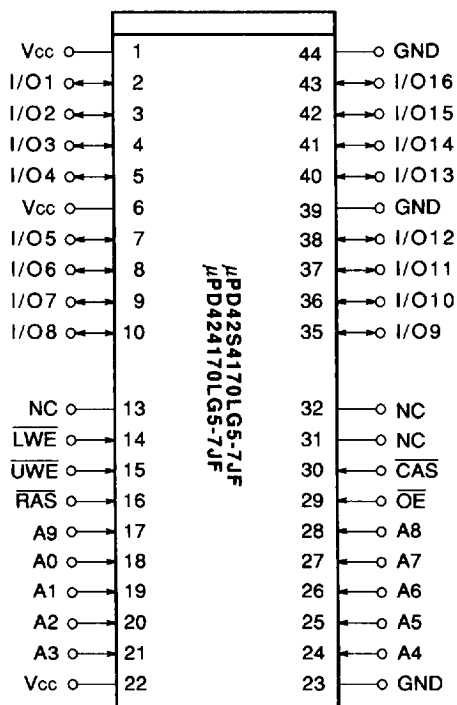
QUALITY GRADE
STANDARD

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

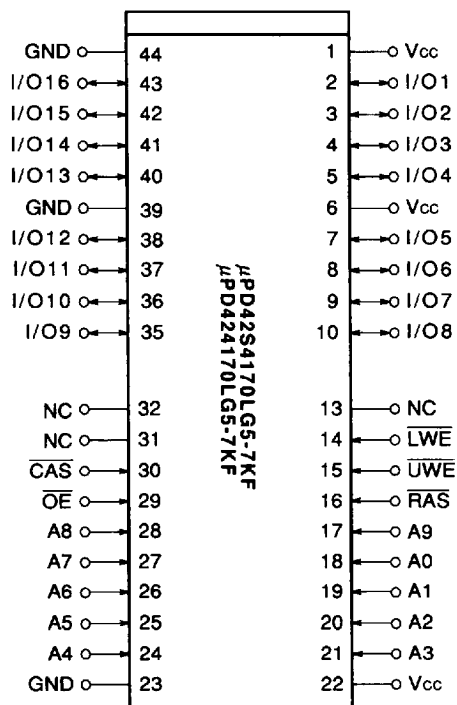


PIN CONFIGURATIONS

44-pin Plastic TSOP
(Marking Side)

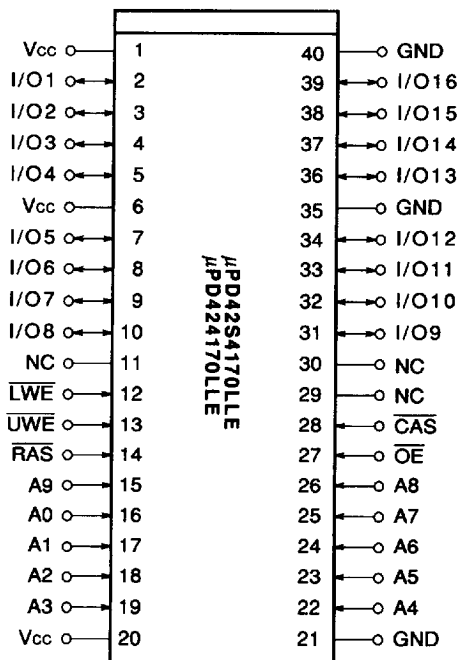


44-pin Plastic TSOP (Reverse bent)
(Marking Side)

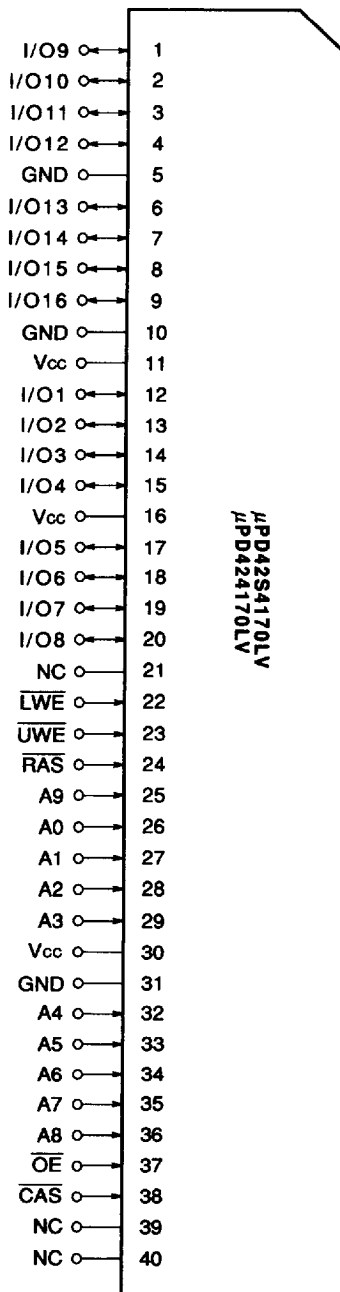


- A0 to A9 : Address Inputs
- I/O1 to I/O16 : Data Inputs/Outputs
- RAS : Row Address Strobe
- CAS : Column Address Strobe
- UWE : Upper Byte Write Enable
- LWE : Lower Byte Write Enable
- OE : Output Enable
- Vcc : Power Supply (+3.3 V ±0.3 V)
- GND : Ground
- NC : No Connection

40-pin Plastic SOJ
(Top View)



40-pin Plastic ZIP
(Front View)



- A0 to A9 : Address Inputs
- I/O1 to I/O16 : Data Inputs/Outputs
- $\overline{\text{RAS}}$: Row Address Strobe
- $\overline{\text{CAS}}$: Column Address Strobe
- $\overline{\text{UWE}}$: Upper Byte Write Enable
- $\overline{\text{LWE}}$: Lower Byte Write Enable
- $\overline{\text{OE}}$: Output Enable
- Vcc : Power Supply (+3.3 V ±0.3 V)
- GND : Ground
- NC : No Connection

ELECTRICAL SPECIFICATIONS NOTE 1

★

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	CONDITION	RATING	UNIT
Voltage on Any Pin Relative to GND	V_T		-0.5 to +4.6	V
Supply Voltage	V_{CC}		-0.5 to +4.6	V
Output Current	I_O		20	mA
Power Dissipation	P_D		1	W
Operating Temperature	T_{opt}		0 to +70	°C
Storage Temperature	T_{stg}		-55 to +125	°C

Remark Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS NOTE 2, 3

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}		3.0	3.3	3.6	V
High Level Input Voltage	V_{IH}		2.0		$V_{CC} + 0.3$	V
Low Level Input Voltage	V_{IL}		-0.3		0.8	V
Ambient Temperature	T_a		0		70	°C

CAPACITANCE ($T_a = +25\text{ }^\circ\text{C}$, $f = 1\text{ MHz}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Capacitance	C_{I1}	A0 to A9			5	pF
	C_{I2}	RAS, CAS, WE, OE			7	pF
Data Input/Output Capacitance	C_D	I/O1 to I/O16			7	pF

★ DC CHARACTERISTICS (Recommended Operating Conditions unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT	NOTE	
Operating current		I _{CC1}	$\overline{\text{RAS}}, \overline{\text{CAS}}$ Cycling $t_{\text{RC}} = t_{\text{RC}(\text{MIN})}$, $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 70 \text{ ns}$	90	mA	4, 5	
				$t_{\text{RAC}} = 80 \text{ ns}$	80			
				$t_{\text{RAC}} = 100 \text{ ns}$	70			
Standby current	μPD42S4170L	I _{CC2}	$V_{\text{IH}(\text{MIN})} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$ $V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$ $I_o = 0 \text{ mA}$	$I_o = 0 \text{ mA}$	0.5	mA		
				$I_o = 0 \text{ mA}$	0.1			
	μPD424170L			$V_{\text{IH}(\text{MIN})} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$			2
				$V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}, \overline{\text{CAS}}$	$I_o = 0 \text{ mA}$			0.5
RAS only refresh current		I _{CC3}	$\overline{\text{RAS}}$ Cycling, $V_{\text{IH}(\text{MIN})} \leq \overline{\text{CAS}}$ $t_{\text{RC}} = t_{\text{RC}(\text{MIN})}$, $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 70 \text{ ns}$	90	mA	4, 5	
				$t_{\text{RAC}} = 80 \text{ ns}$	80			
				$t_{\text{RAC}} = 100 \text{ ns}$	70			
Operating current (Fast page mode)		I _{CC4}	$\overline{\text{RAS}} \leq V_{\text{IL}(\text{MAX})}$ $\overline{\text{CAS}}$ Cycling, $t_{\text{PC}} = t_{\text{PC}(\text{MIN})}$, $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 70 \text{ ns}$	80	mA	4, 5	
				$t_{\text{RAC}} = 80 \text{ ns}$	70			
				$t_{\text{RAC}} = 100 \text{ ns}$	60			
CAS before RAS refresh current		I _{CC5}	$\overline{\text{RAS}}$ Cycling, $t_{\text{RC}} = t_{\text{RC}(\text{MIN})}$, $I_o = 0 \text{ mA}$	$t_{\text{RAC}} = 70 \text{ ns}$	90	mA	4, 5	
				$t_{\text{RAC}} = 80 \text{ ns}$	80			
				$t_{\text{RAC}} = 100 \text{ ns}$	70			
CAS before RAS long refresh current (1 024 cycles/128 ms, only for μPD42S4170L)		I _{CC6}	Standby : $V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{RAS}}$ $V_{\text{CC}} - 0.2 \text{ V} \leq \overline{\text{CAS}}$ or $\text{CAS} \leq 0.2 \text{ V}$ $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh : 1 024 cycles/128 ms $\overline{\text{RAS}}, \overline{\text{CAS}} : 0 \text{ V} \leq V_{\text{IL}} \leq 0.2 \text{ V}$ $V_{\text{CC}} - 0.2 \text{ V} \leq V_{\text{IH}} \leq V_{\text{IH}(\text{MAX})}$ OE: V _{IH} Address input, $\overline{\text{WE}} : V_{\text{IH}}$ or V _{IL} Output : Don't care	$t_{\text{RAS}} \leq 200 \text{ ns}$	100	μA	4, 5	
				$t_{\text{RAS}} \leq 1 \mu\text{s}$	150			
Self refresh current (CAS before RAS self refresh, only for μPD42S4170L)		I _{CC7}	$I_o = 0 \text{ mA}$ $\overline{\text{RAS}}, \overline{\text{CAS}} : 0 \text{ V} \leq V_{\text{IL}} \leq 0.2 \text{ V}$ $V_{\text{CC}} - 0.2 \text{ V} \leq V_{\text{IH}} \leq V_{\text{IH}(\text{MAX})}$		100	μA		
Input leakage current		I _{I(L)}	$V_i = 0 \text{ to } 3.3 \text{ V}$ all other pins except for testing pin = 0 V	-5	+5	μA		
Output leakage current		I _{O(L)}	D _{OUT} is disabled (Hi-Z) $V_o = 0 \text{ to } 3.3 \text{ V}$	-5	+5	μA		
Output high voltage		V _{OH}	$I_o = -2.0 \text{ mA}$	2.4		V		
Output low voltage		V _{OL}	$I_o = 2.0 \text{ mA}$		0.4	V		

AC CHARACTERISTICS

(Recommended Operating Conditions unless otherwise noted) NOTE 6, 7

(1/2)

PARAMETER	SYMBOL	t _{RAC} = 70 ns		t _{RAC} = 80 ns		t _{RAC} = 100 ns		UNIT	NOTE
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Random Read or Write Cycle Time	t _{RC}	130		150		180		ns	8
Read Modify Write Cycle Time	t _{RWC}	175		200		245		ns	8
Fast Page Mode Cycle Time	t _{PC}	45		50		60		ns	8
Read Modify Write Cycle Time (Fast Page Mode)	t _{PRWC}	90		100		120		ns	8
Access Time from $\overline{\text{RAS}}$	t _{RAC}		70		80		100	ns	9, 10
Access Time from $\overline{\text{CAS}}$	t _{CAC}		20		20		25	ns	9, 10
Access Time from Column Address	t _{AA}		35		40		50	ns	9, 10
Access Time from $\overline{\text{CAS}}$ Precharge	t _{ACP}		40		45		55	ns	10
$\overline{\text{CAS}}$ -Output Data Setup Time	t _{CLZ}	0		0		0		ns	10
Output Buffer Turn-off Delay ($\overline{\text{CAS}}$)	t _{OFF}	0	15	0	15	0	20	ns	11
Transition Time (rise and fall)	t _T	3	50	3	50	3	50	ns	
$\overline{\text{RAS}}$ Precharge Time	t _{RP}	50		60		70		ns	
$\overline{\text{RAS}}$ Pulse Width	t _{RAS}	70	10 000	80	10 000	100	10 000	ns	
$\overline{\text{RAS}}$ Pulse Width (Fast Page Mode)	t _{RASP}	70	125 000	80	125 000	100	125 000	ns	
$\overline{\text{RAS}}$ Hold Time	t _{RSH}	20		20		25		ns	
$\overline{\text{CAS}}$ Hold Time	t _{CSH}	70		80		100		ns	
$\overline{\text{CAS}}$ Pulse Width	t _{CAS}	20	10 000	20	10 000	25	10 000	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	t _{RCD}	20	50	20	60	25	75	ns	9
$\overline{\text{RAS}}$ to Column Address Delay Time	t _{RAD}	15	35	15	40	17	50	ns	9
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time	t _{CRP}	10		10		10		ns	12
$\overline{\text{CAS}}$ Precharge Time (Fast Page Mode)	t _{CP}	10		10		10		ns	
Row Address Setup Time	t _{ASR}	0		0		0		ns	
Row Address Hold Time	t _{RAH}	10		10		12		ns	
Column Address Setup Time	t _{ASC}	0		0		0		ns	
Column Address Hold Time	t _{CAH}	15		15		20		ns	
$\overline{\text{CAS}}$ Precharge Time	t _{CPN}	10		10		10		ns	
Column Address Lead Time Referenced to $\overline{\text{RAS}}$	t _{RAL}	35		40		50		ns	
Read Command Setup Time	t _{RCS}	0		0		0		ns	
Read Command Hold Time Referenced to $\overline{\text{CAS}}$	t _{RCH}	0		0		0		ns	13
Read Command Hold Time Referenced to $\overline{\text{RAS}}$	t _{RRH}	0		0		0		ns	13
Write Command Hold Time Referenced to $\overline{\text{CAS}}$	t _{WCH}	10		15		20		ns	14
Write Command Pulse Width	t _{WP}	10		15		20		ns	14
Write Command Lead Time Referenced to $\overline{\text{RAS}}$	t _{RWL}	20		20		25		ns	
Write Command Lead Time Referenced to $\overline{\text{CAS}}$	t _{CWL}	15		15		20		ns	
Data-in Setup Time	t _{DS}	0		0		0		ns	15
Data-in Hold Time	t _{DH}	15		15		20		ns	15

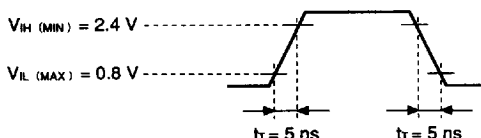
(2/2)

PARAMETER		SYMBOL	t _{RAC} = 70 ns		t _{RAC} = 80 ns		t _{RAC} = 100 ns		UNIT	NOTE
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Refresh Time	μPD42S4170L	t _{REF}		128		128		128	ms	17
	μPD424170L			16		16		16	ms	
Write Command Setup Time		t _{WCS}	0		0		0		ns	16
CAS to WE Delay Time		t _{CWD}	40		45		55		ns	16
RAS to WE Delay Time		t _{RWD}	90		105		130		ns	16
CAS Precharge Delay Time Referenced to WE (Fast Page Mode)		t _{CPWD}	60		70		85		ns	16
Column Address Delay Time Referenced to WE		t _{AWD}	55		65		80		ns	16
CAS Setup Time (CAS before RAS Refresh)		t _{CSR}	5		5		5		ns	
CAS Hold Time (CAS before RAS Refresh)		t _{CHR}	10		10		10		ns	
RAS Precharge CAS Hold Time		t _{RPC}	10		10		10		ns	
OE to RAS inactive Setup Time		t _{OES}	0		0		0		ns	
Access Time from OE		t _{OEA}		20		20		25	ns	
OE Data Delay Time		t _{OED}	15		15		20		ns	
Output Buffer Turn-off Delay (OE)		t _{OEZ}	0	15	0	15	0	20	ns	11
OE Output Data Setup Time		t _{OLZ}	0		0		0		ns	
OE Hold Time		t _{OEH}	0		0		0		ns	
Masked Write Setup Time		t _{MCS}	0		0		0		ns	
Masked Byte Hold Time Referenced to RAS		t _{MRH}	0		0		0		ns	
Masked Byte Hold Time Referenced to CAS		t _{MCH}	0		0		0		ns	
RAS Hold Time Referenced to CAS Precharge		t _{RHCP}	40		45		55		ns	
RAS Pulse Width (CAS before RAS Self Refresh)		t _{RASS}	100		100		100		μs	17
RAS Precharge Time (CAS before RAS Self Refresh)		t _{RPS}	130		150		180		ns	17
CAS Hold Time (CAS before RAS Self Refresh)		t _{CHS}	-50		-50		-50		ns	17

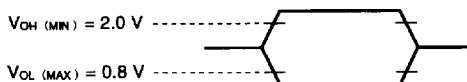
- NOTE**
1. \overline{WE} means \overline{UWE} and \overline{LWE} .
 2. All voltages are referenced to GND.
 3. An initial pause of 100 μs is required after power up followed by 8 \overline{RAS} only refresh cycles before proper device operation is achieved. In case of using internal address refresh counter, a minimum of 8 \overline{CAS} before \overline{RAS} refresh cycles instead of 8 \overline{RAS} only refresh cycles are required.
 4. I_{CC1} , I_{CC3} , I_{CC4} , I_{CC5} and I_{CC6} depend on t_{RC} and t_{PC} . Specified values are obtained with outputs open.
 5. Address can be changed once or less while $\overline{RAS} = V_{IL}$ and $\overline{CAS} = V_{IH}$.
 6. AC measurements assume $t_r = 5$ ns.
 7. AC Characteristics test condition



(1) Input timing specification



(2) Output timing specification



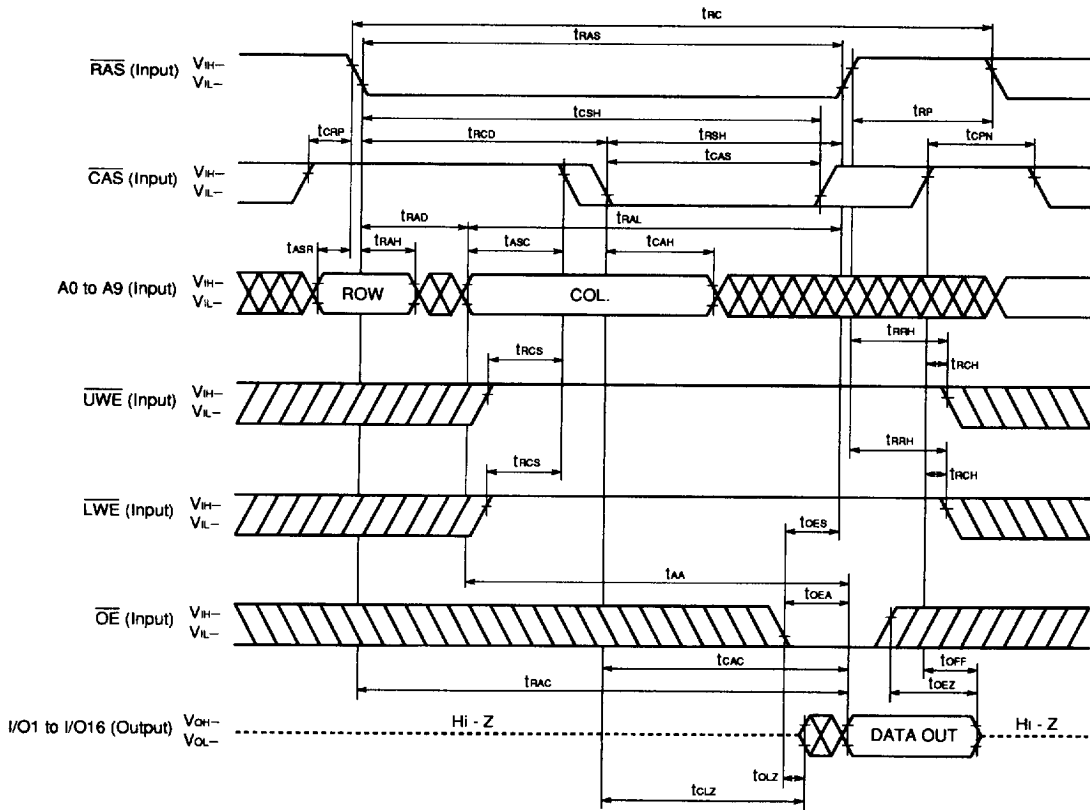
8. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range ($T_a = 0$ to 70 °C) is assured.
9. In random read cycle, the access time is changed by the conditions of t_{RAD} and t_{RCD} as follows.

CONDITION	ACCESS TIME
$t_{RAD} \leq t_{RAD} (MAX.)$ and $t_{RCD} \leq t_{RCD} (MAX.)$	$t_{RAC} (MAX.)$
$t_{RAD} (MAX.) \leq t_{RAD}$ and $t_{RCD} \leq t_{RCD} (MAX.)$	$t_{AA} (MAX.)$
$t_{RCD} (MAX.) \leq t_{RCD}$	$t_{CAC} (MAX.)$

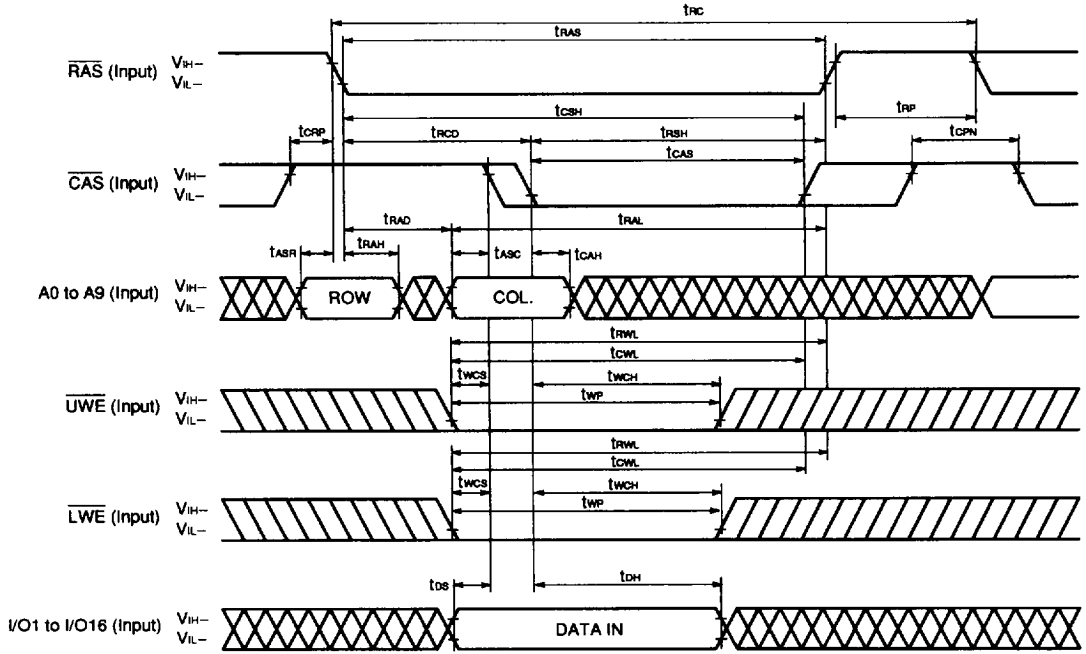
$t_{RAD} (MAX.)$ and $t_{RCD} (MAX.)$ indicate the points which the access time changes and are not the limits of operation.

10. Loading conditions are 1TTL and 100 pF.
11. $t_{OFF} (MAX.)$ and $t_{OEZ} (MAX.)$ define the time at which the output achieves the open circuit condition and are not referenced to V_{OH} or V_{OL} .
12. $t_{CRP} (MIN.)$ requirement should be applicable for $\overline{RAS}/\overline{CAS}$ cycles preceded by any cycles.
13. Either $t_{RCH} (MIN.)$ or $t_{RRH} (MIN.)$ must be satisfied for a read cycle.
14. $t_{WP} (MIN.)$ is applicable for late write cycle or read modify write cycle. In early write cycles, $t_{WCH} (MIN.)$ should be satisfied.
15. This specification is referenced to \overline{CAS} falling edge in early write cycles and to \overline{WE} falling edge in late write or read modify write cycles.
16. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} (MIN.) \leq t_{WCS}$, the cycle is an early write cycle and the data out pins will remain Hi-Z through the entire cycle. If $t_{RWD} (MIN.) \leq t_{RWD}$, $t_{CWD} (MIN.) \leq t_{CWD}$, $t_{AWD} (MIN.) \leq t_{AWD}$, and $t_{CPWD} (MIN.) \leq t_{CPWD}$, the cycle is a read modify write cycle and condition of the data out (at access time) is indeterminate.
17. This specification is applicable only for μPD42S4170L.

READ CYCLE

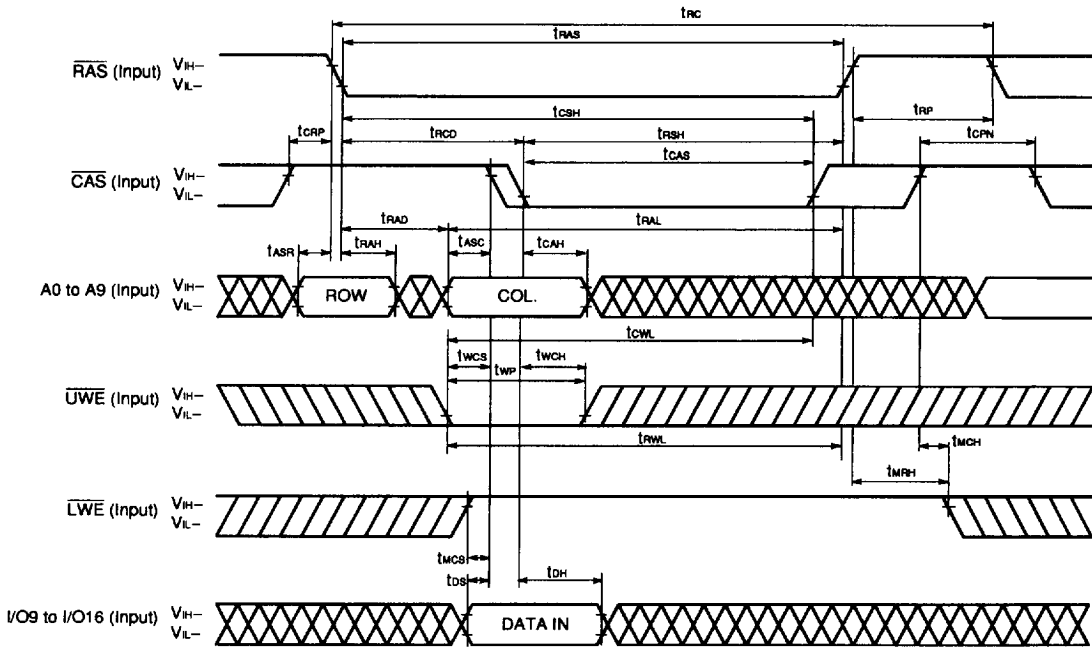


EARLY WRITE CYCLE



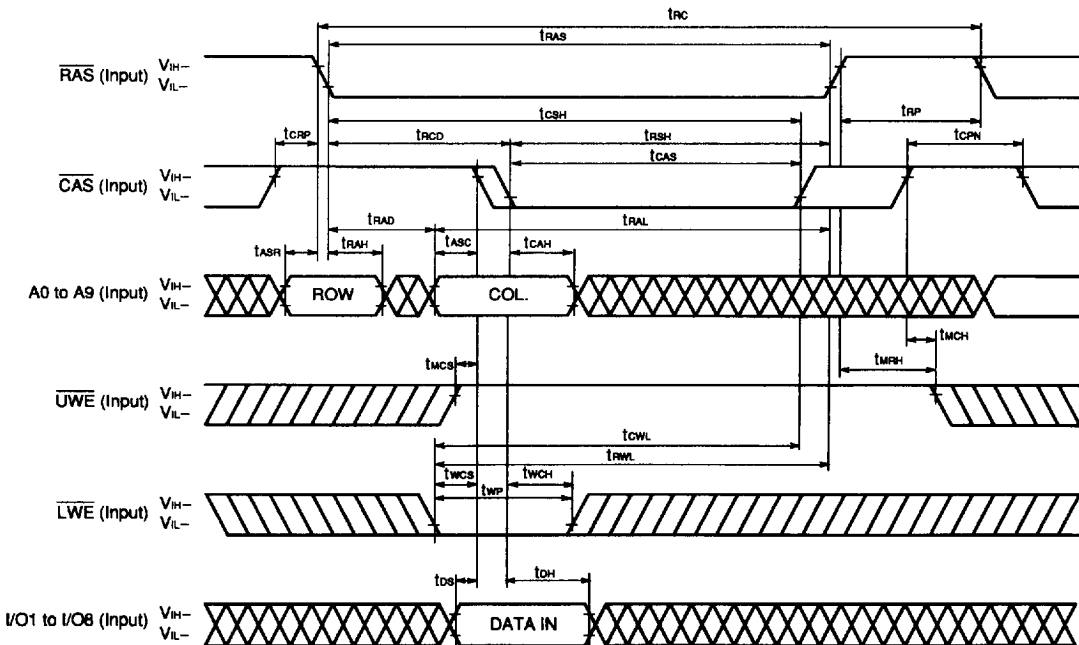
Remark \overline{OE} = Don't care

UPPER BYTE EARLY WRITE CYCLE



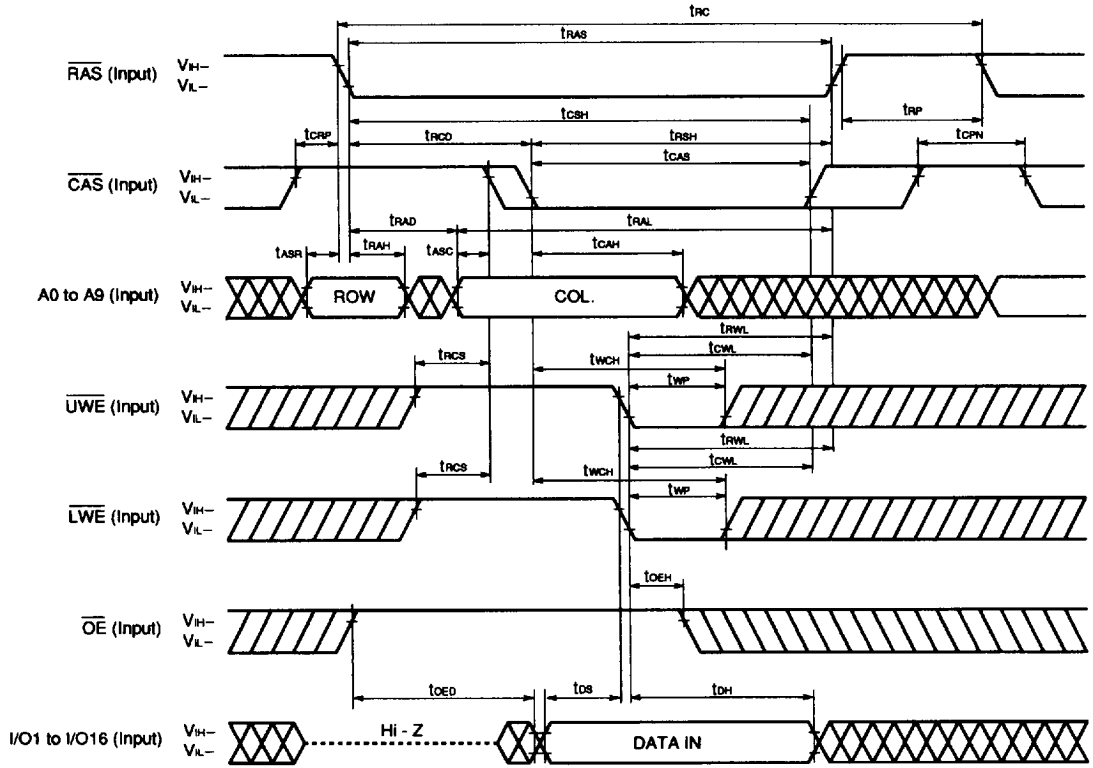
Remark \overline{OE} , I/O1 to I/O8 = Don't care

LOWER BYTE EARLY WRITE CYCLE

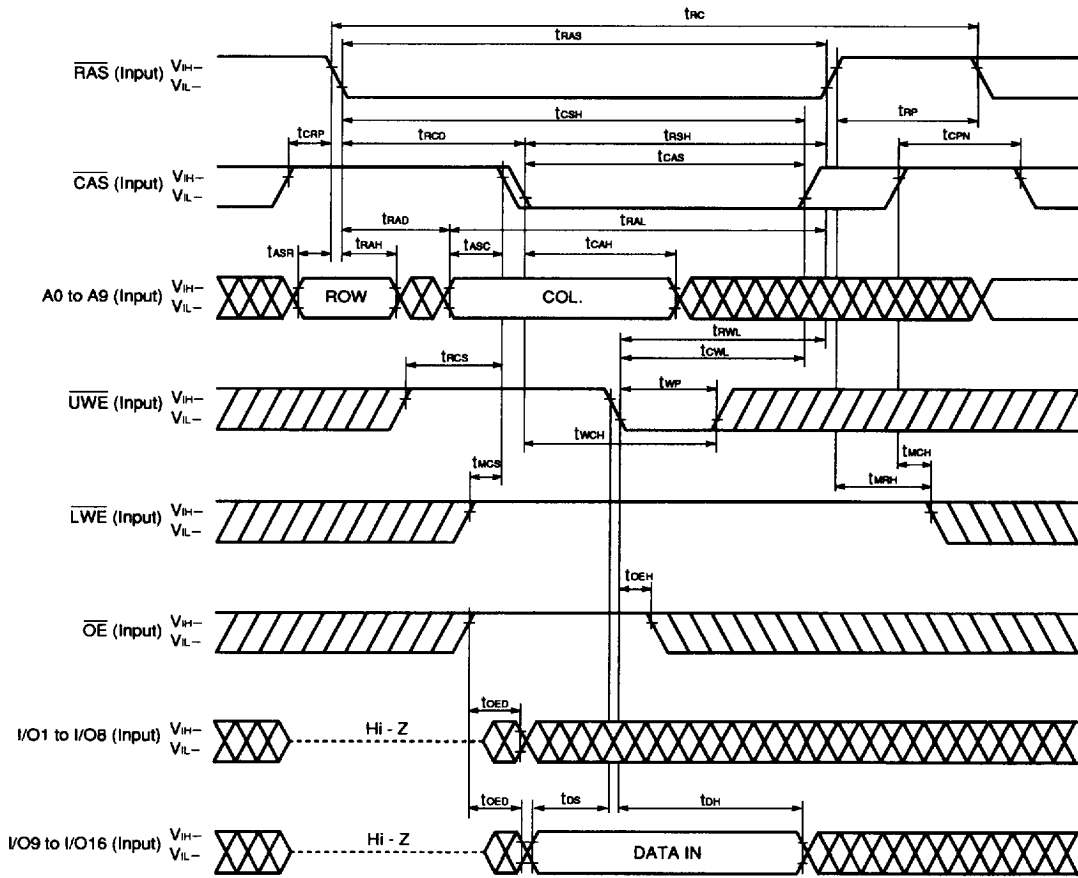


Remark \overline{OE} , I/O9 to I/O16 = Don't care

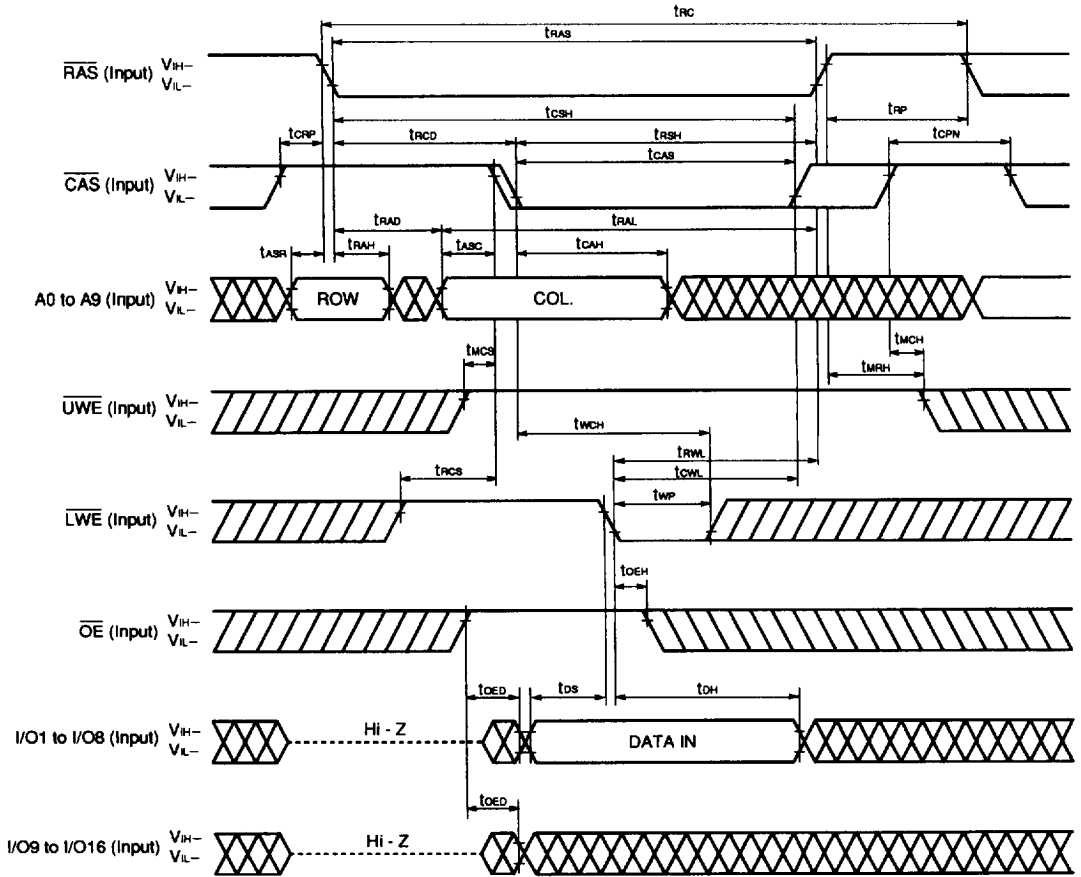
LATE WRITE CYCLE



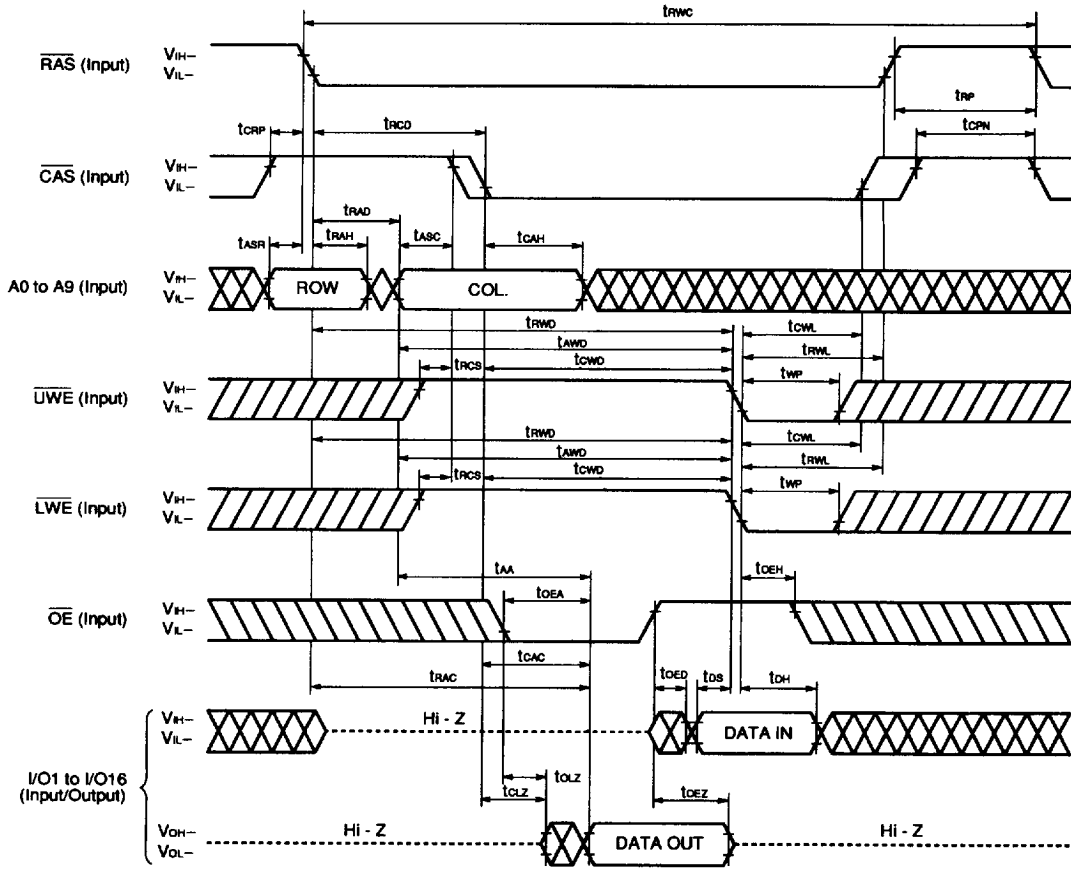
UPPER BYTE LATE WRITE CYCLE



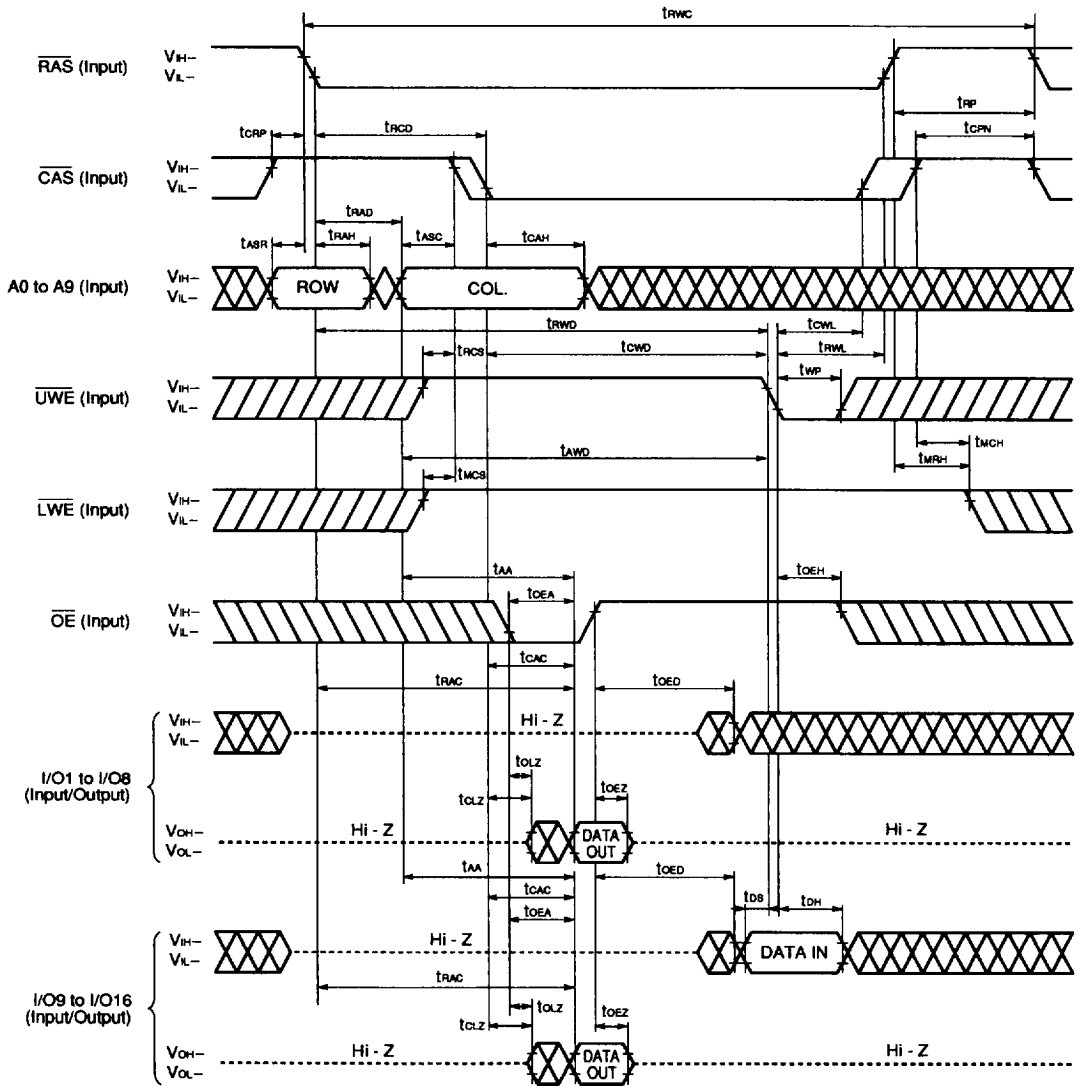
LOWER BYTE LATE WRITE CYCLE



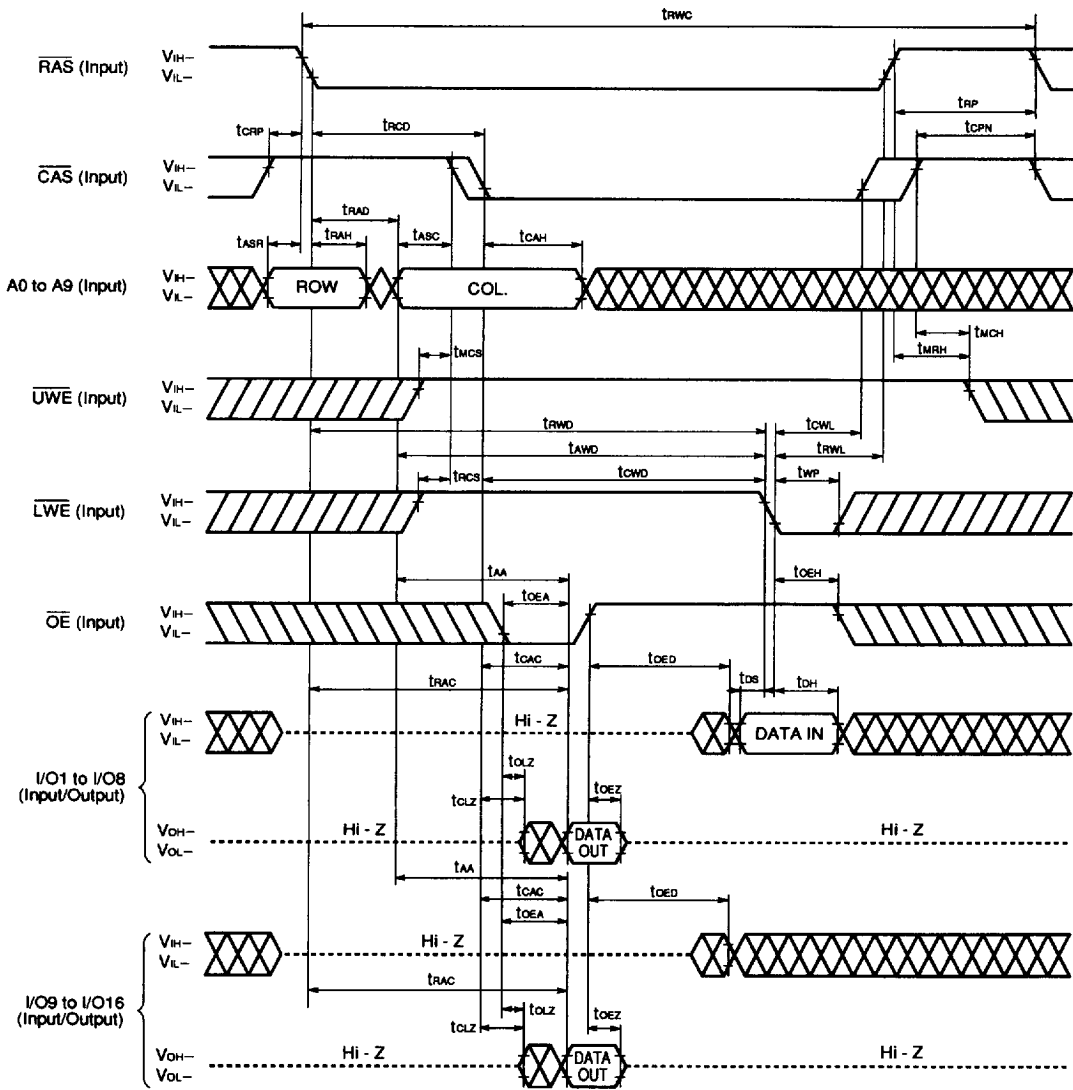
READ MODIFY WRITE CYCLE



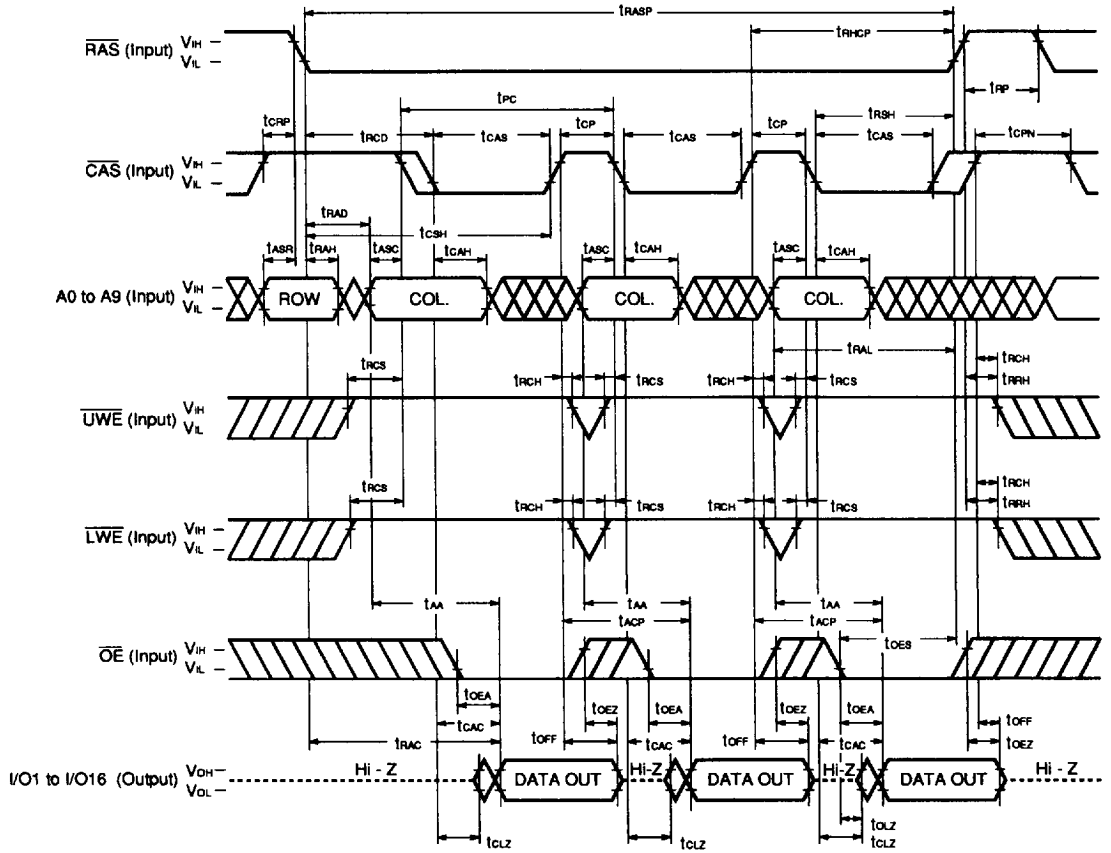
UPPER BYTE READ MODIFY WRITE CYCLE



LOWER BYTE READ MODIFY WRITE CYCLE

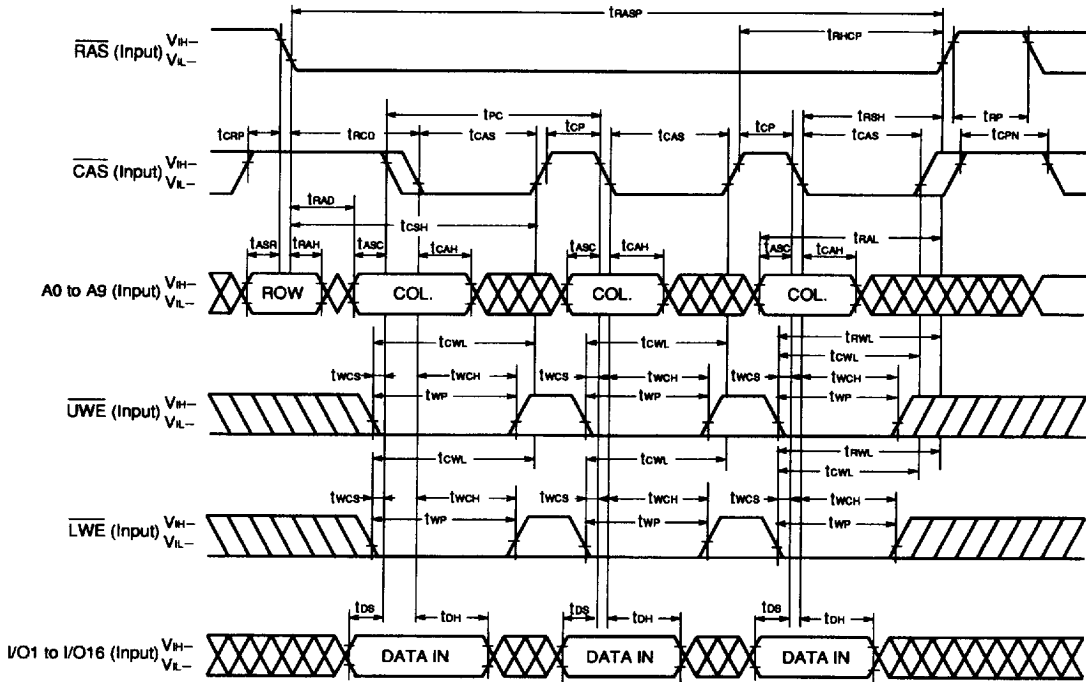


FAST PAGE MODE READ CYCLE



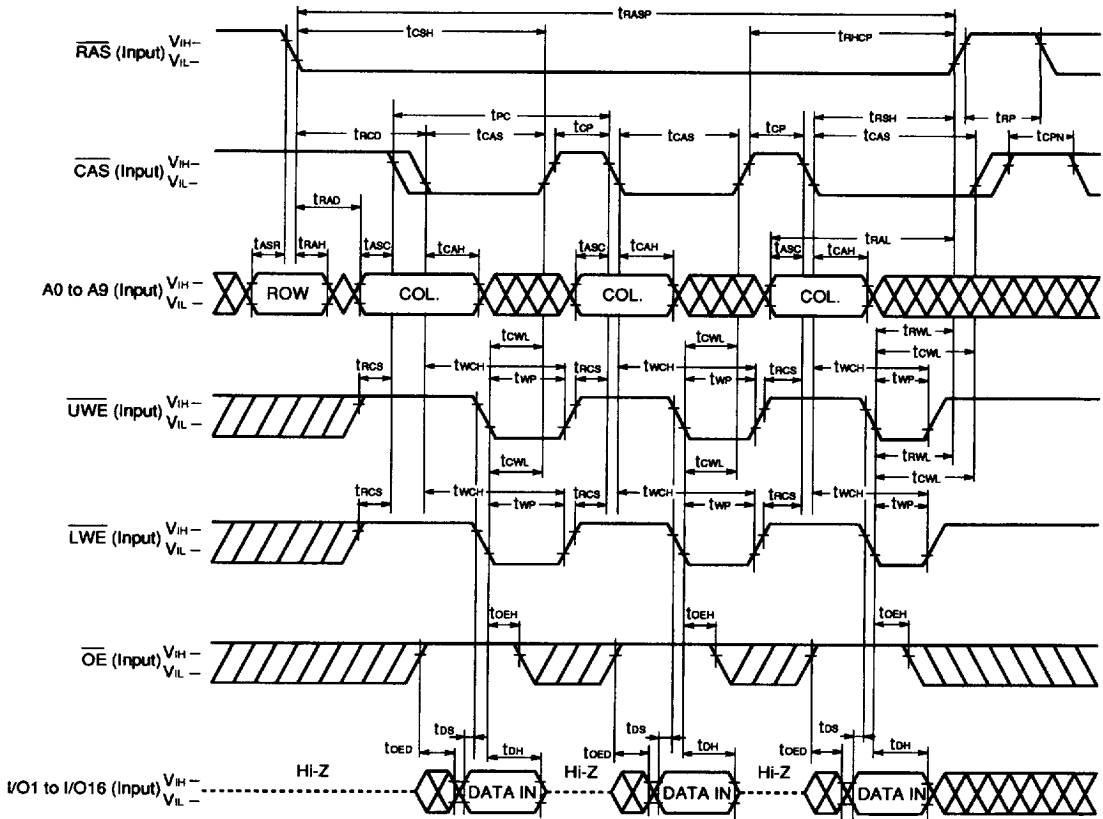
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

FAST PAGE MODE EARLY WRITE CYCLE



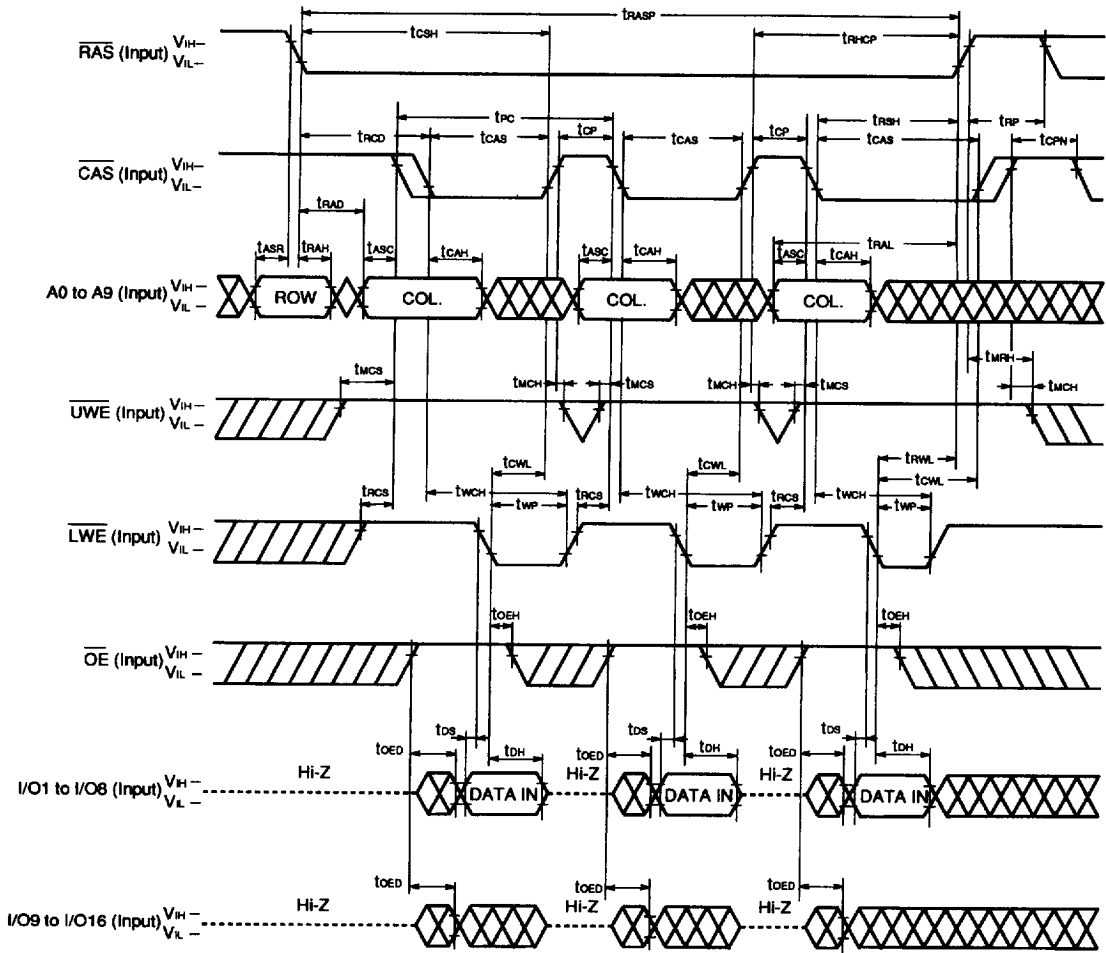
Remark \overline{OE} = Don't care
 In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

FAST PAGE MODE LATE WRITE CYCLE



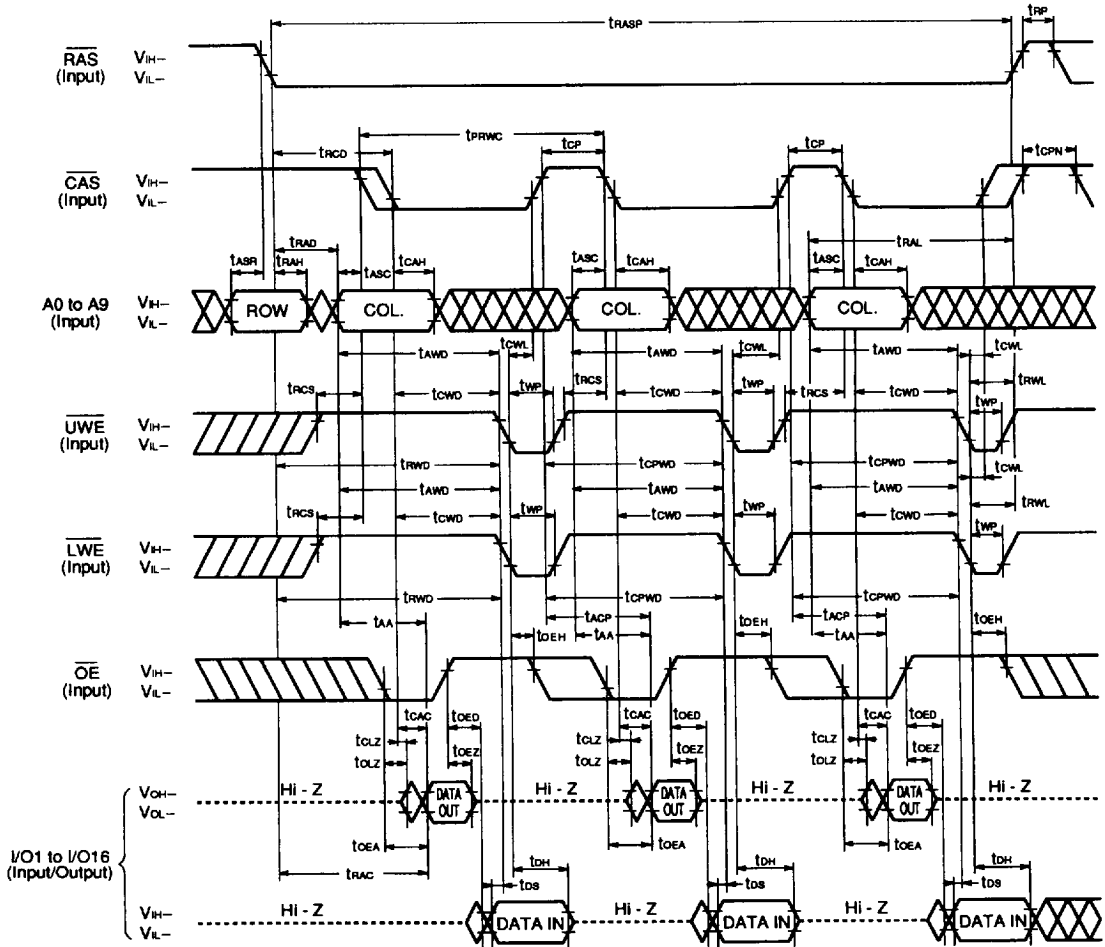
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

FAST PAGE MODE LOWER BYTE LATE WRITE CYCLE



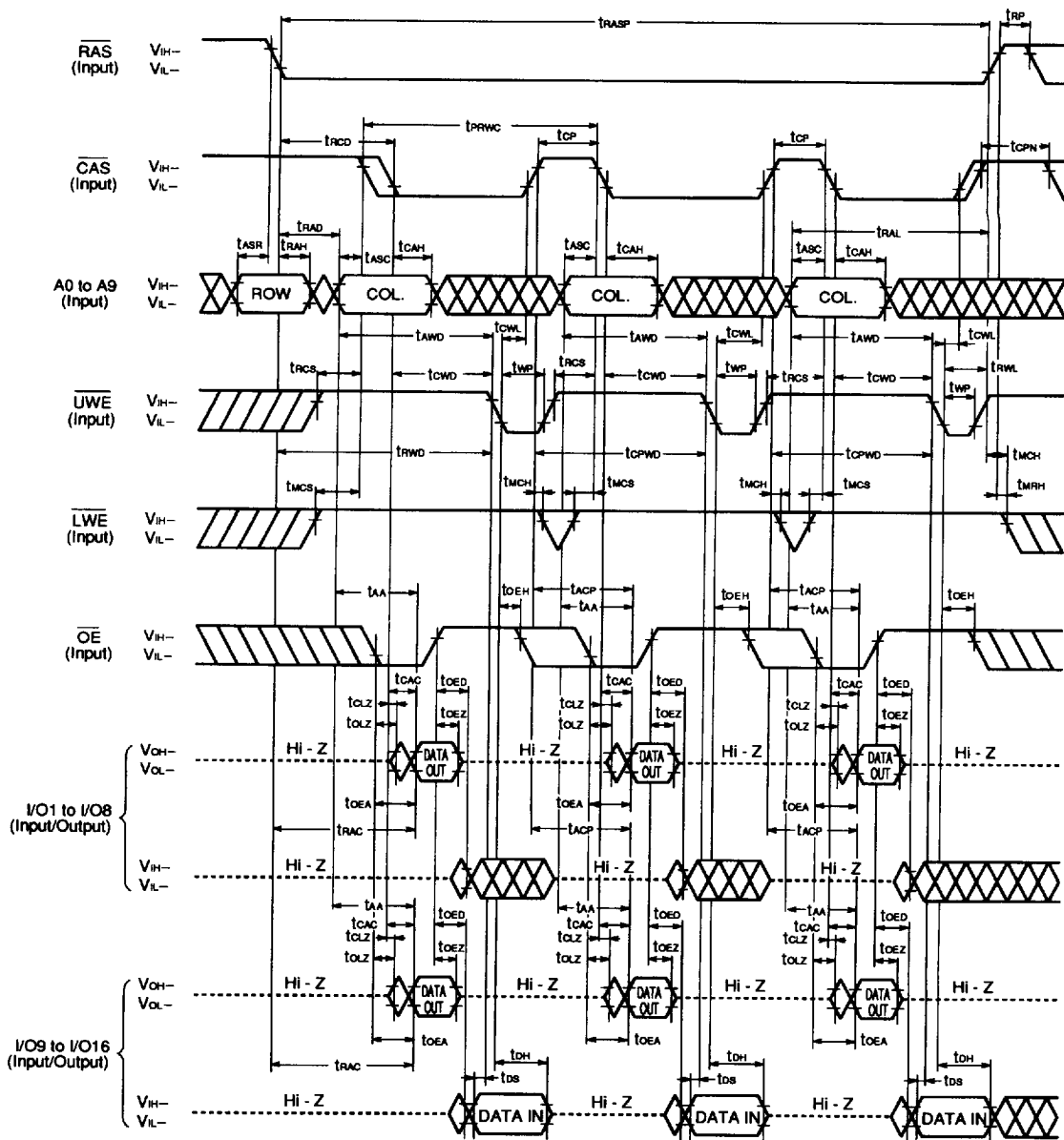
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{\text{CAS}}$ cycles within the same $\overline{\text{RAS}}$ cycle.

FAST PAGE MODE READ MODIFY WRITE CYCLE



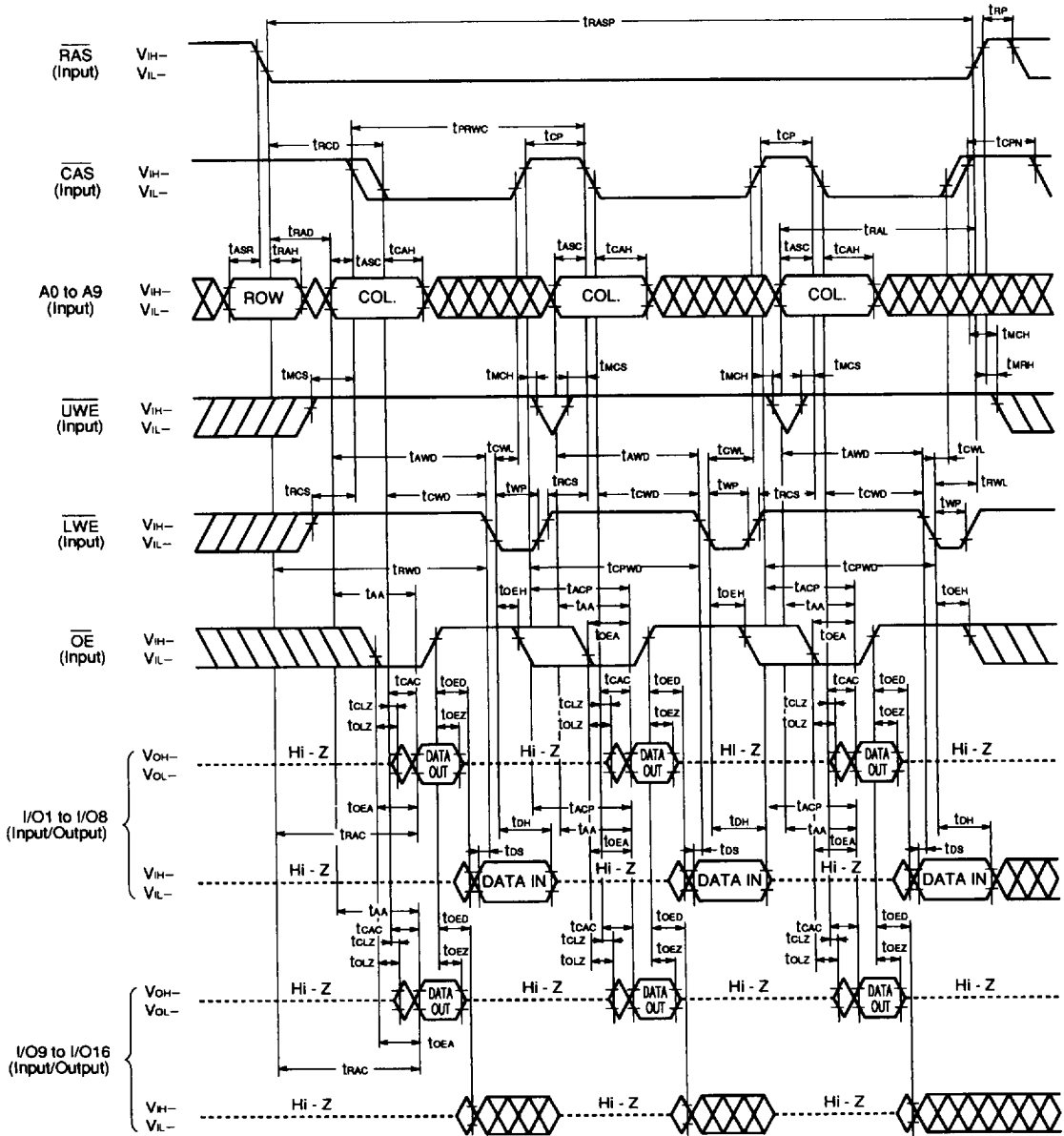
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

FAST PAGE MODE UPPER BYTE READ MODIFY WRITE CYCLE



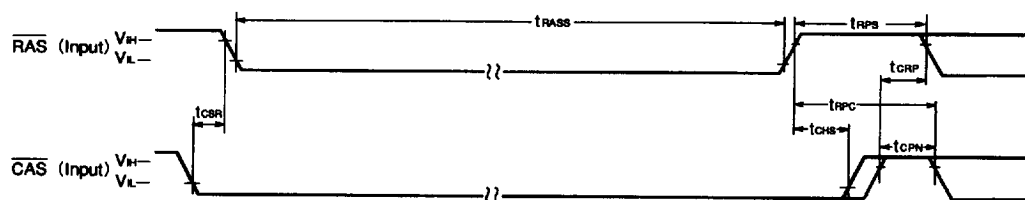
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle.

FAST PAGE MODE LOWER BYTE READ MODIFY WRITE CYCLE



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive CAS cycles within the same RAS cycle

★ **CAS BEFORE RAS SELF REFRESH CYCLE (Only for μPD42S4170L)**



Remark Address, \overline{UWE} , \overline{LWE} , \overline{OE} = Don't care I/O1 to I/O16 = HI-Z

How to use the CAS before RAS self refresh mode.

CAS before RAS self refresh mode can't be used by itself. It must be used with performing one of 3 refreshes below.

• **In case of using distributed CAS before RAS refresh**

Refresh 1 024 times during 128 ms before set into the CAS before RAS self refresh mode and after reset.

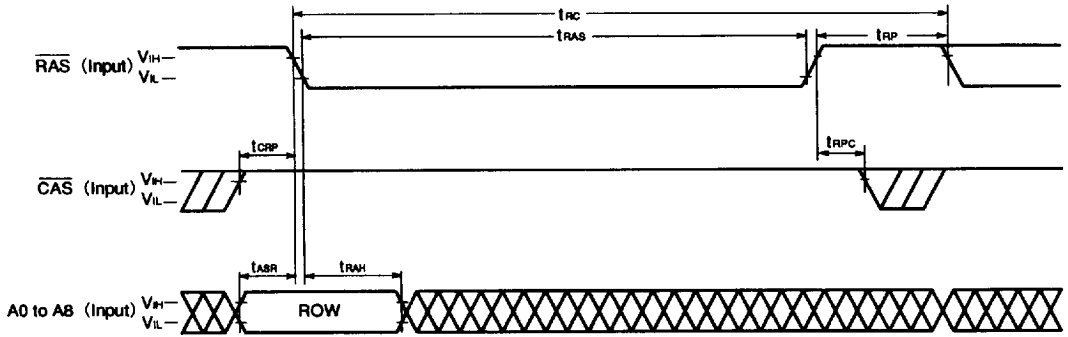
• **In case of using burst CAS before RAS refresh**

Refresh 1 024 times during 16 ms before set into the CAS before RAS self refresh mode and after reset.

• **In case of using RAS only refresh**

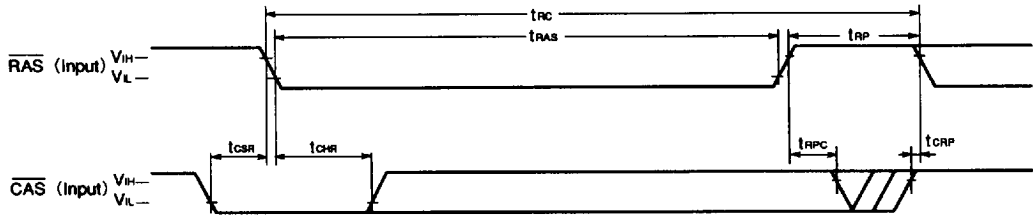
Refresh all refresh addresses during 16 ms before set into the CAS before RAS self refresh mode and after reset.

RAS ONLY REFRESH CYCLE



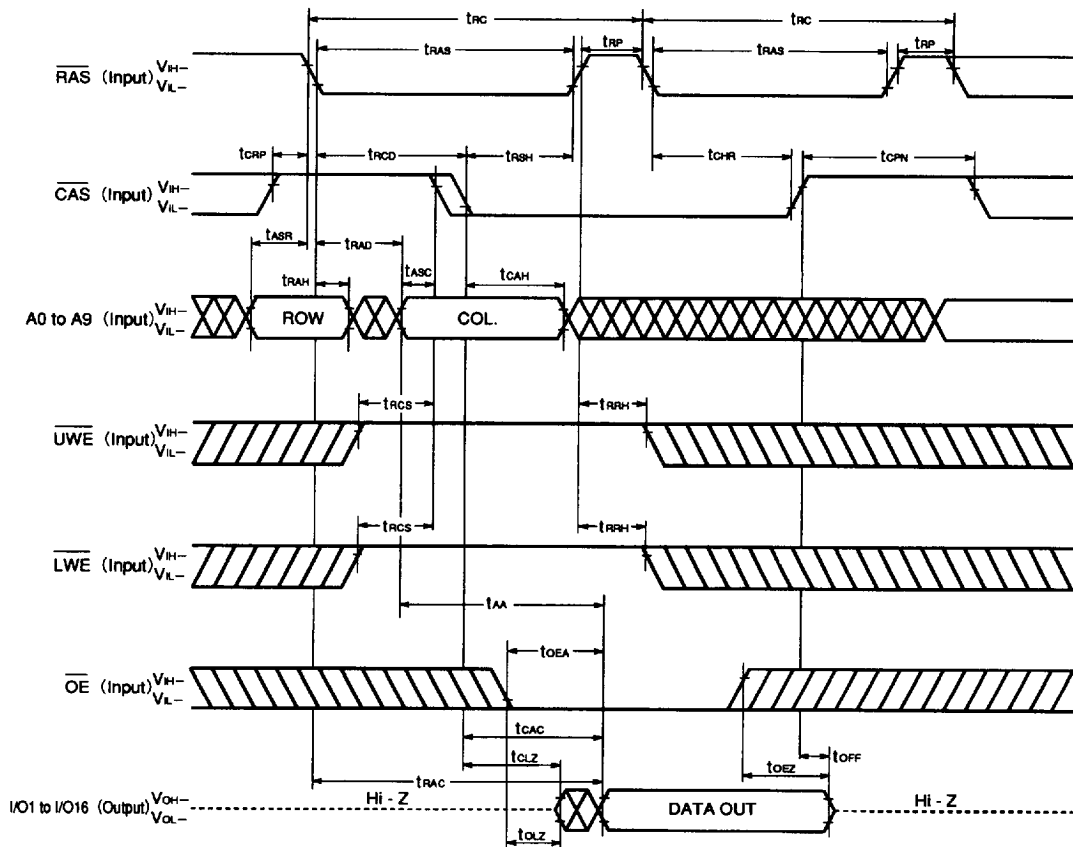
Remark \overline{UWE} , \overline{LWE} , \overline{OE} = Don't care
I/O1 to I/O16 = Hi-Z

CAS BEFORE RAS REFRESH CYCLE

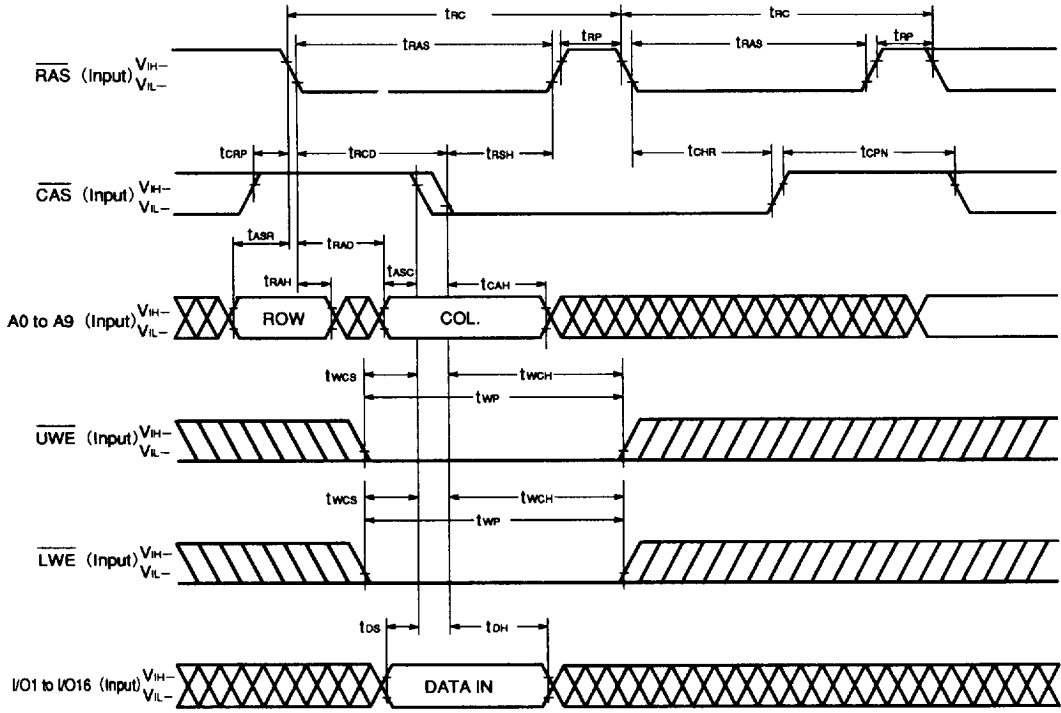


Remark A0 to A9, \overline{UWE} , \overline{LWE} , \overline{OE} = Don't care I/O1 to I/O16 = Hi-Z

CAS BEFORE RAS HIDDEN REFRESH CYCLE (READ)

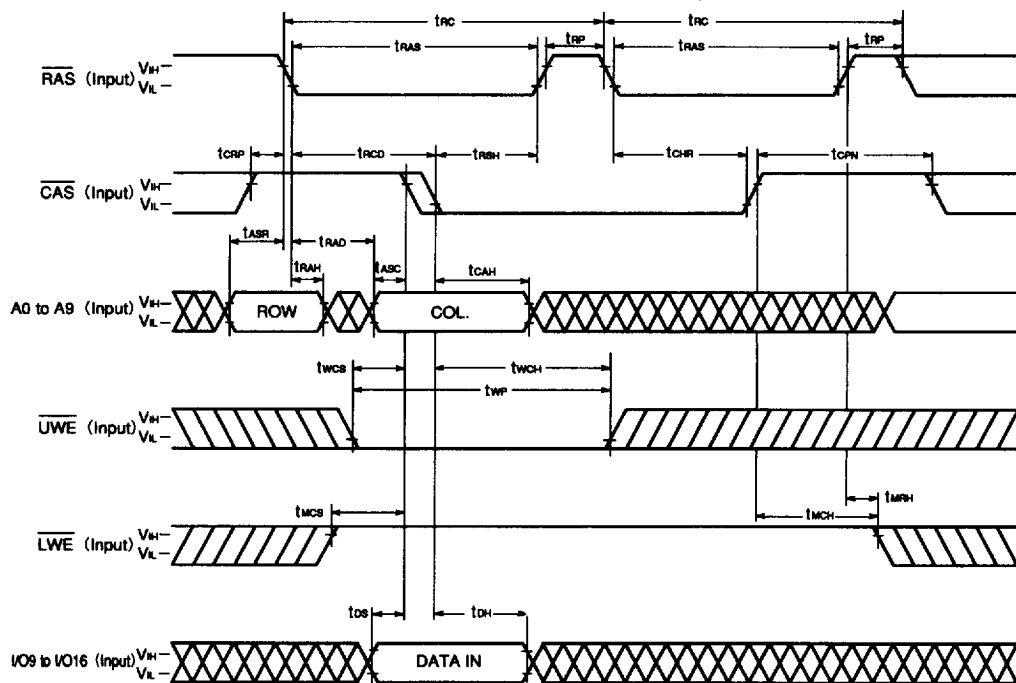


CAS BEFORE RAS HIDDEN REFRESH CYCLE (WRITE)



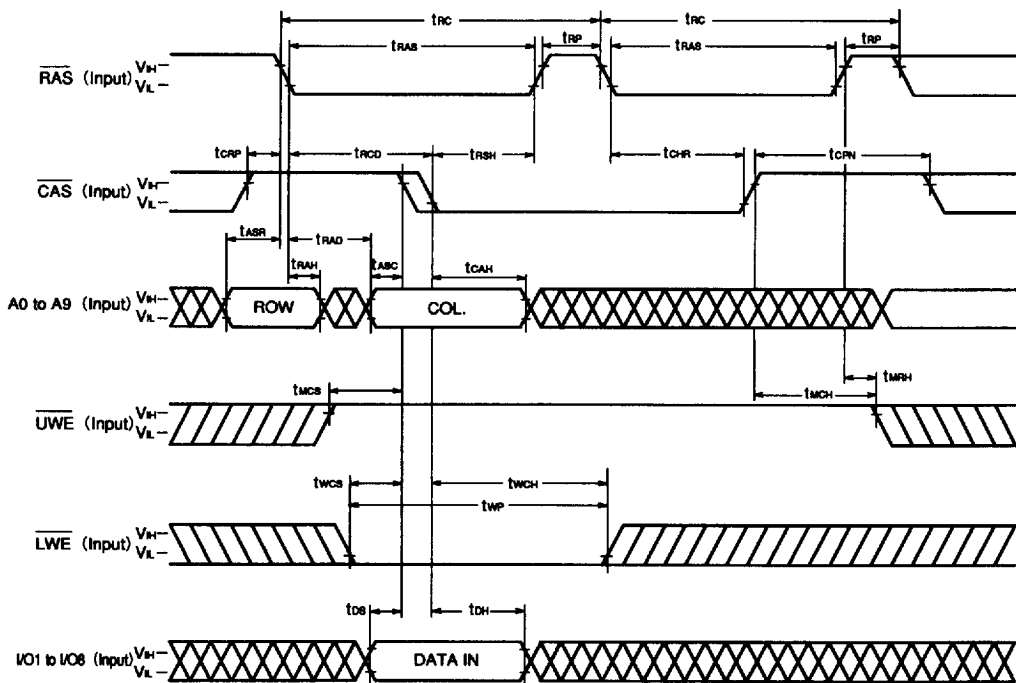
Remark \overline{OE} = Don't care

CAS BEFORE RAS HIDDEN REFRESH CYCLE (UPPER BYTE WRITE)



Remark \overline{OE} , I/O1 to I/O8 = Don't care

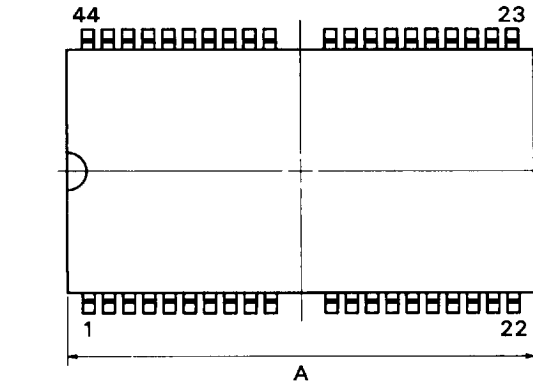
CAS BEFORE RAS HIDDEN REFRESH CYCLE (LOWER BYTE WRITE)



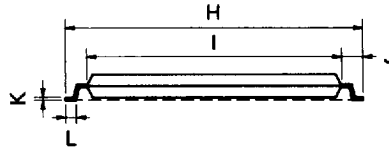
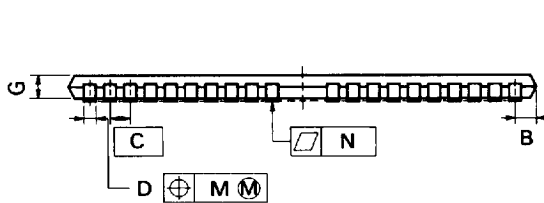
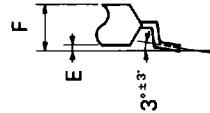
Remark \overline{OE} , I/O9 to I/O16 = Don't care

PACKAGE INFORMATION

44 PIN PLASTIC TSOP (400mil)



detail of lead end



S44G5-80-7JF

NOTE

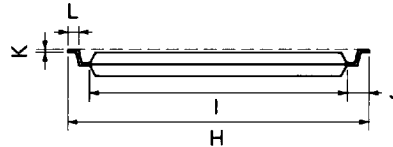
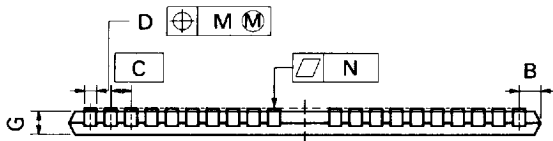
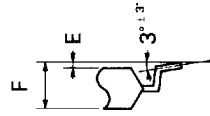
Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.0 MAX.	0.040 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30 ^{±0.10}	0.012 ^{+0.004} _{-0.006}
E	0.05 ^{±0.06}	0.002 ^{±0.002}
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76 ^{±0.2}	0.463 ^{±0.008}
I	10.16 ^{±0.1}	0.400 ^{±0.004}
J	0.8 ^{±0.2}	0.031 ^{+0.008} _{-0.008}
K	0.125 ^{+0.10} _{-0.08}	0.005 ^{+0.004} _{-0.002}
L	0.5 ^{±0.1}	0.020 ^{+0.004} _{-0.006}
M	0.13	0.005
N	0.10	0.004

44 PIN PLASTIC TSOP (400mil)



detail of lead end



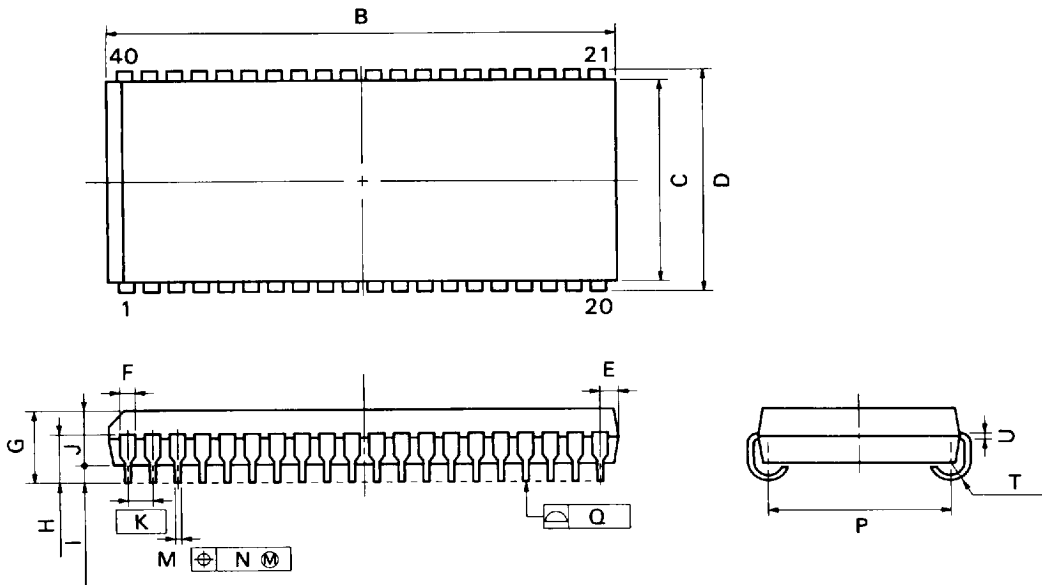
S44G5-80-7KF

NOTE

Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	18.81 MAX.	0.741 MAX.
B	1.0 MAX.	0.040 MAX.
C	0.8 (T.P.)	0.031 (T.P.)
D	0.30 ^{+0.10}	0.012 ^{-0.004} _{-0.006}
E	0.05 ^{±0.05}	0.002 ^{±0.002}
F	1.1 MAX.	0.044 MAX.
G	0.97	0.038
H	11.76 ^{±0.2}	0.463 ^{±0.008}
I	10.16 ^{±0.1}	0.400 ^{±0.004}
J	0.8 ^{±0.2}	0.031 ^{-0.008} _{-0.009}
K	0.125 ^{-0.10} _{-0.05}	0.005 ^{-0.004} _{-0.002}
L	0.5 ^{±0.1}	0.020 ^{-0.004} _{-0.005}
M	0.13	0.005
N	0.10	0.004

40PIN PLASTIC SOJ (400 mil)



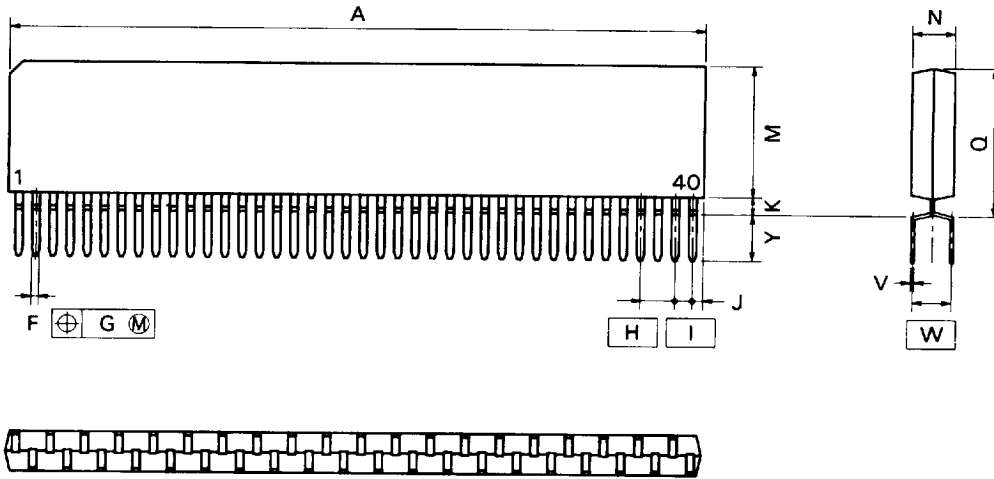
P40LE-400A-1

NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	26.29 ^{+0.2} _{-0.35}	1.035 ^{+0.008} _{-0.014}
C	10.16	0.400
D	11.18 ^{+0.2}	0.440 ^{+0.008}
E	1.08 ^{±0.15}	0.043 ^{+0.006} _{-0.007}
F	0.7	0.028
G	3.5 ^{±0.2}	0.138 ^{+0.008}
H	2.4 ^{±0.2}	0.094 ^{+0.009} _{-0.008}
I	0.8 MIN.	0.031 MIN
J	2.6	0.102
K	1.27(T.P.)	0.050(T.P.)
M	0.40 ^{±0.10}	0.016 ^{+0.004} _{-0.005}
N	0.12	0.005
P	9.4 ^{+0.20}	0.370 ^{+0.008}
Q	0.15	0.006
T	R 0.85	R 0.033
U	0.20 ^{+0.10} _{-0.08}	0.008 ^{+0.004} _{-0.002}

40 PIN PLASTIC ZIP(475mil)



NOTE

Each lead centerline is located within 0.25 mm (0.010 inch) of its true position (T.P.) at maximum material condition.

P40V-100-475A

ITEM	MILLIMETERS	INCHES
A	51.23 MAX.	2.017 MAX.
F	0.50 ^{+0.10}	0.020 ^{+0.004}
G	0.25	0.010
H	2.54 (T.P.)	0.100 (T.P.)
I	1.27 (T.P.)	0.050 (T.P.)
J	0.85 MAX.	0.034 MAX.
K	0.9 MIN.	0.035 MIN.
M	10.5 MAX.	0.414 MAX.
N	2.8 ^{+0.2}	0.110 ^{+0.008}
Q	12.07 MAX.	0.476 MAX.
V	0.25 ^{+0.10}	0.010 ^{+0.004}
W	2.54 (T.P.)	0.100 (T.P.)
Y	3.25 ^{+0.2}	0.128 ^{+0.008}

RECOMMENDED SOLDERING CONDITIONS

Please consult with our sales offices when soldering μ PD42S4170L, 424170L.

TYPE OF SURFACE MOUNT DEVICE

μ PD42S4170LG5, 424170LG5 (44-pin Plastic TSOP)

μ PD42S4170LLE, 424170LLE (40-pin Plastic SOJ)

TYPE OF THROUGH HOLE MOUNT DEVICE

μ PD42S4170LV, 424170LV (40-pin Plastic ZIP)